DISCRETE SEMICONDUCTORS

DATA SHEET

BUT11APX-1200Silicon Diffused Power Transistor

Product specification

April 1999



Silicon Diffused Power Transistor

BUT11APX-1200

GENERAL DESCRIPTION

Enhanced performance new generation, high voltage, high-speed switching npn transistor in a plastic full-pack envelope intended for use in horizontal deflection circuits of colour television receivers. Features exceptional tolerance to base drive and collector current load variations resulting in a very low worst case dissipation.

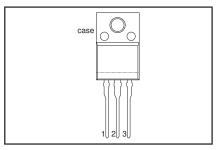
QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_{CESM}	Collector-emitter voltage peak value	$V_{BF} = 0 \text{ V}$	-	1200	V
V _{CBO}	Collector-Base voltage (open emitter)		-	1200	V
V _{CEO}	Collector-emitter voltage (open base)		-	550	V
I _C	Collector current (DC)		-	6	A
1 1	Collector current peak value		-	10	Α
Pin	Total power dissipation	T _{bs} ≤ 25 °C	-	32	W
P _{tot} V _{CEsat}	Collector-emitter saturation voltage	$T_{hs} \le 25 ^{\circ}C$ $I_{C} = 2 A; I_{B} = 0.4 A$	0.15	1.0	V
h _{FEsat}	DC current gain	$I_{\rm C} = 3 \text{ A}; \bar{V}_{\rm CF} = 5 \text{ V}$	15.5	-	
t _f	Fall time	$I_{C} = 3 \text{ A}; V_{CE} = 5 \text{ V}$ $I_{C} = 2.5 \text{ A}; I_{B1} = 0.5 \text{ A}$	170	300	ns

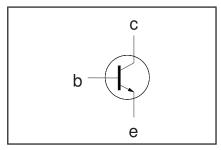
PINNING - SOT186A

PIN	DESCRIPTION	
1	base	
2	collector	
3	emitter	
case	isolated	

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CESM}	Collector to emitter voltage Collector to emitter voltage (open base)	$V_{BE} = 0 V$	- -	1200 550	V
V _{CBO}	Collector to base voltage (open emitter) Collector current (DC)		-	1200	V A
I _{CM}	Collector current peak value Base current (DC) Base current peak value		-	10 3 5	A A A
P _{tot} T _{stg}	Total power dissipation Storage temperature	$T_{hs} \le 25 ^{\circ}C$	- -65	32 150	, C
Tisig	Junction temperature		-	150	°Č

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
R _{th i-hs}	Junction to heatsink	with heatsink compound	-	3.95	K/W
R _{th i-a}	Junction to ambient	in free air	55	-	K/W

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ISOLATION LIMITING VALUE & CHARACTERISTIC

 T_{hs} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{isol}	R.M.S. isolation voltage from all three terminals to external heatsink	f = 50-60 Hz; sinusoidal waveform; R.H. ≤ 65%; clean and dustfree	1	1	2500	V
C _{isol}	Capacitance from T2 to external heatsink	f = 1 MHz	-	10	-	pF

STATIC CHARACTERISTICS

T_{hs} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CES}	Collector cut-off current ¹	$V_{BE} = 0 \text{ V}; V_{CE} = V_{CESMmax}, V_{BE} = 0 \text{ V}; V_{CE} = V_{CESMmax};$	-	-	1.0 2.0	mA mA
${ m I}_{ m EBO} \ { m V}_{ m CEOsust}$	Emitter cut-off current Collector-emitter sustaining voltage	$T_i = 125 ^{\circ}\text{C}$ $V_{EB} = 7 ^{\circ}\text{V}; I_C = 0 ^{\circ}\text{A}$ $I_B = 0 ^{\circ}\text{A}; I_C = 10 ^{\circ}\text{mA};$	- 550	- -	0.1	mA V
V _{CEsat} V _{BEsat} h _{FE} h _{FE}	Collector-emitter saturation voltage Base-emitter saturation voltage DC current gain	$ \begin{array}{l} L = 25 \text{ mH} \\ I_C = 2.0 \text{ A}; \ I_B = 0.4 \text{ A} \\ I_C = 2.0 \text{ A}; \ I_B = 0.4 \text{ A} \\ I_C = 1 \text{ mA}; \ V_{CE} = 5 \text{ V} \\ I_C = 500 \text{ mA}; \ V_{CE} = 5 \text{ V} \\ \end{array} $	- - 13 20	0.15 0.91 25 30	1.0 1.5 - 47	V V
h _{FEsat} h _{FEsat}	DC current gain	$I_{C} = 3.0 \text{ A}; V_{CE} = 5 \text{ V}$ $I_{C} = 2 \text{ A}; V_{CE} = 5 \text{ V}$ $I_{C} = 3.0 \text{ A}; V_{CE} = 5 \text{ V}$	13	18.5 15.5	25 -	

DYNAMIC CHARACTERISTICS

 $T_{hs} = 25$ °C unless otherwise specified8

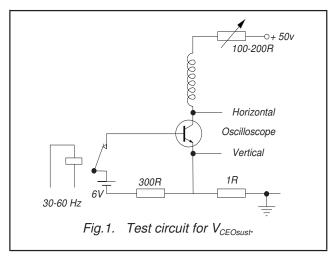
SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
	Switching times (resistive load)	$I_{Con} = 2.5 \text{ A}; I_{Bon} = -I_{Boff} = 0.5 \text{ A}; $ $R_L = 75 \text{ ohms}; V_{BB2} = 4 \text{ V};$			
t _{on}	Turn-on time		-	0.5	μs
ι _s	Turn-off storage time Turn-off fall time		-	0.3	μs us
u _f				0.5	μο
	Switching times (inductive load)	$I_{Csat} = 2.5 \text{ A}; I_{B1} = 0.5 \text{ A}; L_{B} = 1 \mu\text{H}; $ - $V_{BB} = 5 \text{ V}$			
t _s	Turn-off storage time	- 55 -	-	1.5	μs
t_{f}	Turn-off fall time		170	300	ns
	Switching times (inductive load)	$I_{Csat} = 2.5 \text{ A}; I_{B1} = 0.5 \text{ A}; L_{B} = 1 \mu\text{H}; \\ -V_{BB} = 5 \text{ V}; T_{i} = 100 ^{\circ}\text{C}$			
l t _s	Turn-off storage time		-	1.8	μs
t _f	Turn-off fall time		-	300	ns

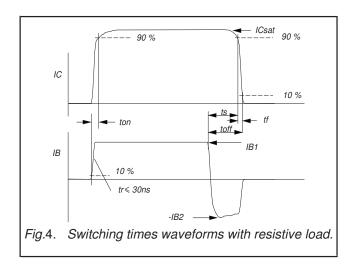
April 1999 2 Rev 1.000

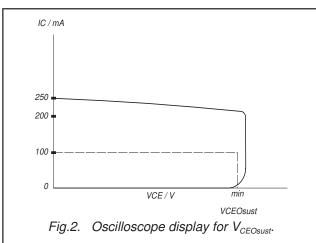
 $^{{\}bf 1} \ {\bf Measured} \ {\bf with} \ {\bf half} \ {\bf sine}\hbox{-}{\bf wave} \ {\bf voltage} \ ({\bf curve} \ {\bf tracer}).$

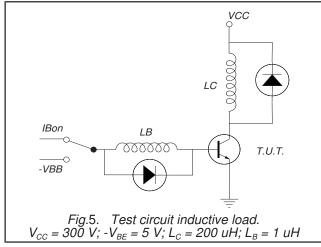
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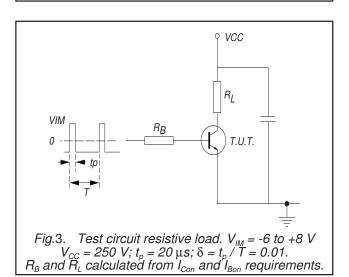
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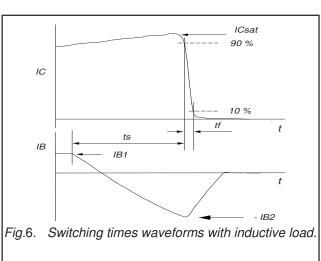






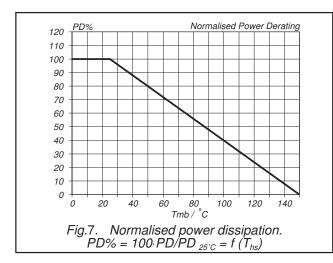


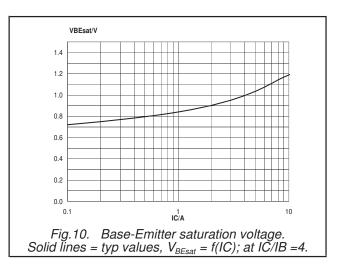


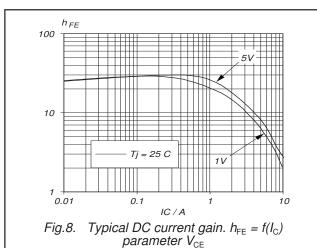


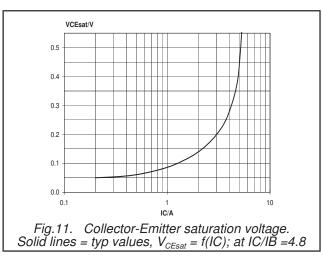
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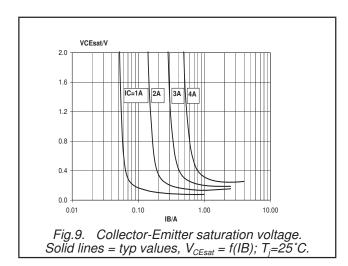
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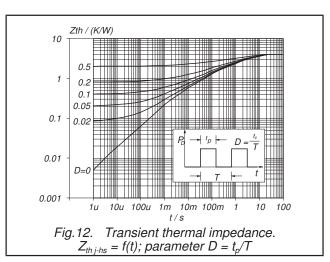






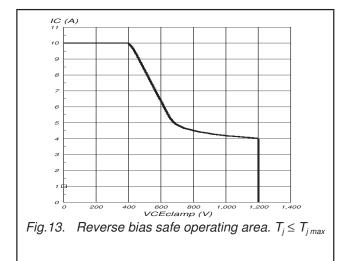






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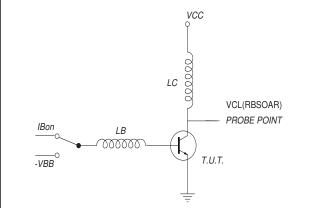
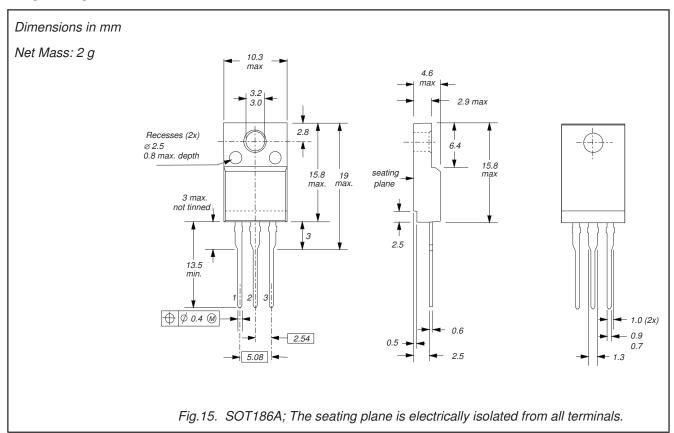


Fig.14. Test circuit for reverse bias safe operating area. $V_{cl} \leq$ 1200V; $V_{cc} =$ 150V; $V_{BB} =$ -5V; $L_B =$ 1 μ H; $L_c =$ 200 μ H

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MECHANICAL DATA



- Refer to mounting instructions for F-pack envelopes.
 Epoxy meets UL94 V0 at 1/8".

Legal information

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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